

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b> (Use several sheets if necessary)	Docket Number: 12364.36US01	Application Number: 10/023418
	Applicant: LEE et al.	
	Filing Date: 17 December 2001	Group Art Unit: 1754 1753



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U.S. PATENT DOCUMENTS						
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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
SHV			Seeger et al., "Fabrication of silicon cones and pillars using rough metal films as plasma etching masks," <i>Applied Physics Letters</i> , 74:11, 1627-1629 (March 1999).			
SHV			Okuyama et al., "Indium phosphide whiskers grown by ion bombardment," <i>Surface Science</i> , 338, L857-L862 (1995).			
SAV			Fujimoto et al., "Geometry and structure of sputter-induced cones on nickelseeded silicon," <i>J. Appl. Phys.</i> , 77:6, 2725-2734 (March 1995).			
SHV			Floro et al., "Ion-bombardment-induced whisker formation on graphite," <i>J. Vac. Sci. Technol.</i> , 1:3, 1398-1402 (July-Sept 1983).			
SAV			Hudson, W.R., "Ion beam texturing," <i>J. Vac. Sci. Technol.</i> , 14:1, 286-289 (Jan.-Feb 1977).			
SAV			Kiselev et al., "HREM of nanometric tips prepared from epitaxially grown silicon whiskers," <i>Micron</i> , 28:1, 21-29 (1997).			
SHV			Chen et al., "High-density silicon and silicon nitride cones," <i>J. of Crystal Growth</i> , 210, 527-531 (2000).			
SAV			Whitton et al., "The production of regular pyramids on argon ion bombarded surfaces of copper crystals," <i>Applications of Surface Science</i> , 1, 408-413 (1978).			
SAV			Beckey, H.D., "Experimental techniques in field ionisation and field desorption mass spectrometry," <i>J. Phys. E.</i> (1979).			



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EXAMINER <u>Steven H. Ver Steeg</u>	DATE CONSIDERED <u>April 23, 2003</u>
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